ABSTRACT

A circuit and method for selecting reference voltages in a semiconductor memory device, in which an internal voltage or a high voltage can be changed by use of a plurality of reference voltage generators therewith, so as to enable the selection of mutually different reference voltages. In one embodiment, the circuit comprises a plural number of reference voltage generators for generating first and second reference voltages; an internal voltage generator for receiving the first or second reference voltage, and generating an internal voltage of a constant level; and a high voltage generator for receiving and boosting the first or second reference voltage, and generating the high voltage VPP of a given level. In such construction, one reference voltage out of the first and second reference voltages is selected and input to the high voltage generator, and one reference voltage out of the first and second reference voltages is selected and input to the internal voltage generator, in response to a reference voltage selection signal supplied to the device.